L Number	Hits	Search Text	DB	Time stamp
-	2993	fowler near5 Nordheim near5 tunnel$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:02
-	2825	(fowler near5 Nordheim near5 tunnel$4) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:03
-	1697	((fowler near5 Nordheim near5 tunnel$4) and memory) and (insulation insulating insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:16
-	1500	(((fowler near5 Nordheim near5 tunnel$4) and memory) and (insulation insulating insulator)) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:04
-	718	((((fowler near5 Nordheim near5 tunnel$4) and memory) and (insulation insulating insulator)) and transistor) and MOS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:14
-	823	(fowler near5 Nordheim near5 tunnel$4) and (MOS near5 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:15
-	537	((fowler near5 Nordheim near5 tunnel$4) and (MOS near5 transistor)) and (insulation insulating insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:17
-	498	(((fowler near5 Nordheim near5 tunnel$4) and (MOS near5 transistor)) and (insulation insulating insulator)) and (floating near5 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:18
-	475	((((fowler near5 Nordheim near5 tunnel$4) and (MOS near5 transistor)) and (insulation insulating insulator)) and (floating near5 gate)) and (control near5 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 09:52
-	104	(((((fowler near5 Nordheim near5 tunnel$4) and (MOS near5 transistor)) and (insulation insulating insulator)) and (floating near5 gate)) and (control near5 gate)) and (poly near5 (gate block))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 11:07
-	943	(fowler near5 Nordheim near5 tunnel$4) and (((metal adj oxide adj semiconductor) MOS) near5 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 11:08
-	778	((fowler near5 Nordheim near5 tunnel$4) and (((metal adj oxide adj semiconductor) MOS) near5 transistor)) and (control adj gate) and (floating adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 11:10
-	524	(((fowler near5 Nordheim near5 tunnel$4) and (((metal adj oxide adj semiconductor) MOS) near5 transistor)) and (control adj gate) and (floating adj gate)) and (insulator insulation insulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 11:14
-	348	((((fowler near5 Nordheim near5 tunnel$4) and (((metal adj oxide adj semiconductor) MOS) near5 transistor)) and (control adj gate) and (floating adj gate)) and (insulator insulation insulating)) and ((poly polysilicon) near5 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/10/16 11:15